Advance Information

Surface Mount Schottky Power Rectifier

POWERMITE® Power Surface Mount Package

The Schottky Powermite employs the Schottky Barrier principle with a barrier metal and epitaxial construction that produces optimal forward voltage drop—reverse current tradeoff. The advanced packaging techniques provide for a highly efficient micro miniature, space saving surface mount Rectifier. With its unique heatsink design, the Powermite has the same thermal performance as the SMA while being 50% smaller in footprint area, and delivering one of the lowest height profiles, < 1.1 mm in the industry. Because of its small size, it is ideal for use in portable and battery powered products such as cellular and cordless phones, chargers, notebook computers, printers, PDAs and PCMCIA cards. Typical applications are ac/dc and dc—dc converters, reverse battery protection, and "Oring" of multiple supply voltages and any other application where performance and size are critical.

Features:

- Low Profile Maximum Height of 1.1 mm
- Small Footprint Footprint Area of 8.45 mm2
- Low V_F Provides Higher Efficiency and Extends Battery Life
- Supplied in 12 mm Tape and Reel 12,000 Units per Reel
- Low Thermal Resistance with Direct Thermal Path of Die on Exposed Cathode Heat Sink

Mechanical Characteristics:

- Powermite is JEDEC Registered as D0-216AA
- Case: Molded Epoxy
- Epoxy Meets UL94, VO at 1/8"
- Weight: 62 mg (approximately)
- Device Marking: BCJ
- Lead and Mounting Surface Temperature for Soldering Purposes. 260°C Maximum for 10 Seconds



ON Semiconductor

Formerly a Division of Motorola http://onsemi.com

SCHOTTKY BARRIER
RECTIFIER
1.0 AMPERES
40 VOLTS



PLASTIC CASE 457

ORDERING INFORMATION

Device	Package	Shipping
MBRM140T3	Plastic	12,000 Units per 12 mm Tape & Reel

This document contains information on a new product. Specifications and information herein are subject to change without notice.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	40	V
Average Rectified Forward Current (At Rated V _R , T _C = 110°C)	Io	1.0	А
Peak Repetitive Forward Current (At Rated V _R , Square Wave, 100 kHz, T _C = 110°C)	I _{FRM}	2.0	А
Non-Repetitive Peak Surge Current (Non-Repetitive peak surge current, halfwave, single phase, 60 Hz)	I _{FSM}	50	А
Storage Temperature	T _{stg}	-55 to 150	°C
Operating Junction Temperature	TJ	-55 to 125	°C
Voltage Rate of Change (Rated V _R , T _J = 25°C)	dv/dt	10,000	V/μs

THERMAL CHARACTERISTICS

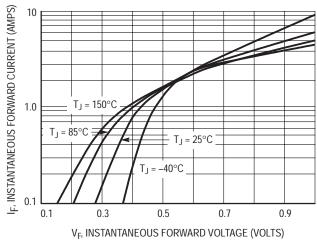
Thermal Resistance – Junction–to–Lead (Anode) (1)	R _{til}	35	°C/W	
Thermal Resistance – Junction–to–Tab (Cathode) (1)	R _{titab}	23		ı
Thermal Resistance – Junction–to–Ambient (1)	Ř _{tja}	277		ı

⁽¹⁾ Mounted with minimum recommended pad size, PC Board FR4, See Figures 9 & 10.

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage (2), See Figure 2	V _F	T _J = 25°C	T _J = 85°C	V
$(I_F = 0.1 \text{ A})$ $(I_F = 1.0 \text{ A})$ $(I_F = 3.0 \text{ A})$		0.36 0.55 0.85	0.30 0.515 0.88	
Maximum Instantaneous Reverse Current, See Figure 4	I _R	T _J = 25°C	T _J = 85°C	mA
$(V_R = 40 \text{ V})$ $(V_R = 20 \text{ V})$		0.5 0.15	25 18	

⁽²⁾ Pulse Test: Pulse Width \leq 250 μ s, Duty Cycle \leq 2%.



1.0 T_J = 150°C

T_J = 85°C

T_J = 25°C

T_J = 25°C

V_F, MAXIMUM INSTANTANEOUS FORWARD VOLTAGE (VOLTS)

Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage

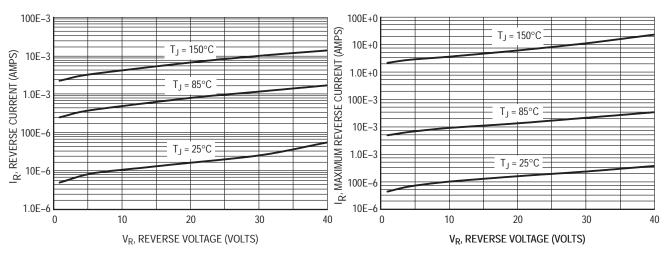
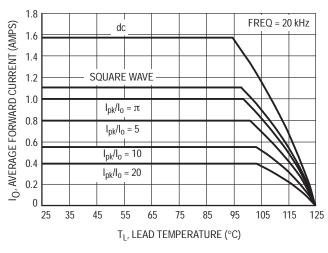


Figure 3. Typical Reverse Current

Figure 4. Maximum Reverse Current



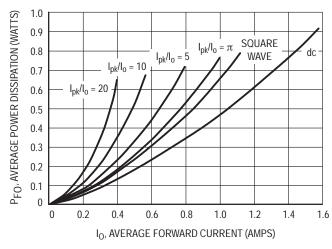
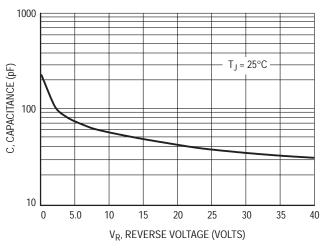


Figure 5. Current Derating

Figure 6. Forward Power Dissipation



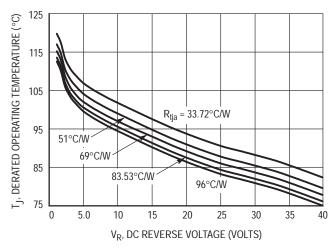


Figure 7. Capacitance

Figure 8. Typical Operating Temperature Derating*

r(t) = thermal impedance under given conditions,

Pf = forward power dissipation, and

Pr = reverse power dissipation

This graph displays the derated allowable T_J due to reverse bias under DC conditions only and is calculated as $T_J = T_{Jmax} - r(t)Pr$, where r(t) = Rthja. For other power applications further calculations must be performed.

^{*} Reverse power dissipation and the possibility of thermal runaway must be considered when operating this device under any reverse voltage conditions. Calculations of T_J therefore must include forward and reverse power effects. The allowable operating T_{LI} may be calculated from the equation: $T_{LI} = T_{LImax} - r(t)(Pf + Pr)$ where

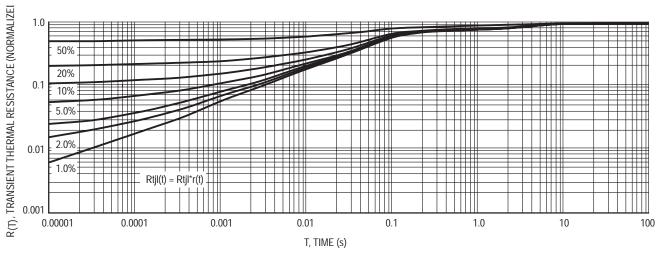


Figure 9. Thermal Response Junction to Lead

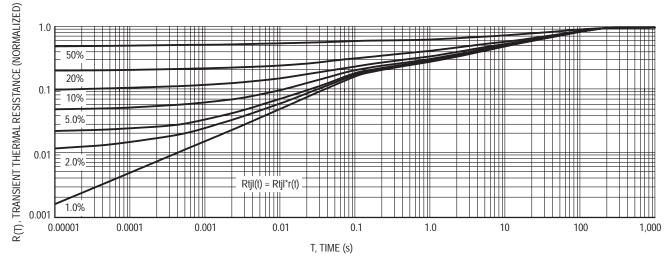
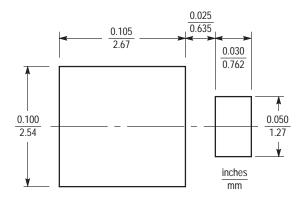


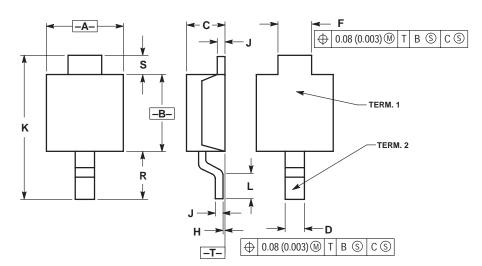
Figure 10. Thermal Response Junction to Ambient



Minimum Recommended Footprint

PACKAGE DIMENSIONS

N SUFFIX PLASTIC PACKAGE CASE 457-04 ISSUE C



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	1.75	2.05	0.069	0.081	
В	1.75	2.18	0.069	0.086	
С	0.85	1.15	0.033	0.045	
D	0.40	0.69	0.016	0.027	
F	0.70	1.00	0.028	0.039	
Н	-0.05	+0.10	-0.002	+0.004	
J	0.10	0.25	0.004	0.010	
K	3.60	3.90	0.142	0.154	
L	0.50	0.80	0.020	0.031	
R	1.20	1.50	0.047	0.059	
S	0.50 RFF		0.019 REF		

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